

# EPIGAP Optronik GmbH

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## Data Sheet

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### Si Avalanche Photodiode

### EOAPD-800-1-07

Rev. 01, 2017

Spectral range	Type	Case
visible-near IR	Si	LCC6 SMD

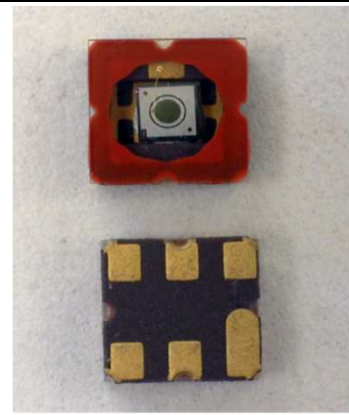
Circular ( $\varnothing 500 \mu\text{m}$ )  $2 \text{ mm}^2$  active area avalanche photodiode optimized sensitivity at 800 nm, housed in a LCC6 SMD package. It is well suited for applications requiring high speed and low noise in visible-near IR applications.

#### Features:

- > Fast Rise Time
- > Ultra Low Noise
- > Low Capacitance
- > High Gain
- > Optimum Gain M100

#### Applications:

- > Optical rangefinders
- > High speed optical communications
- > Medical Equipment
- > Bar Code Readers



### Absolute maximum ratings

Parameters	Symbol	Rating	Unit
Operating temperature range	$T_{\text{OPR}}$	-20...+85	$^{\circ}\text{C}$
Storage temperature range	$T_{\text{STG}}$	-55...+125	$^{\circ}\text{C}$
Power dissipation	$P_{\text{D}}$	1	mW
Storage temperature range	$I_{\text{F}}$	1	mA
Operating voltage	$V_{\text{OP}}$	$0.95 \times V_{\text{BR}}$	V
Lead soldering temperature*	$T_{\text{LS}}$	260	$^{\circ}\text{C}$

\*Time 10 sec max



### Electro-optical characteristics:

$T_{\text{amb}} = 25^{\circ}\text{C}$ , unless otherwise specified

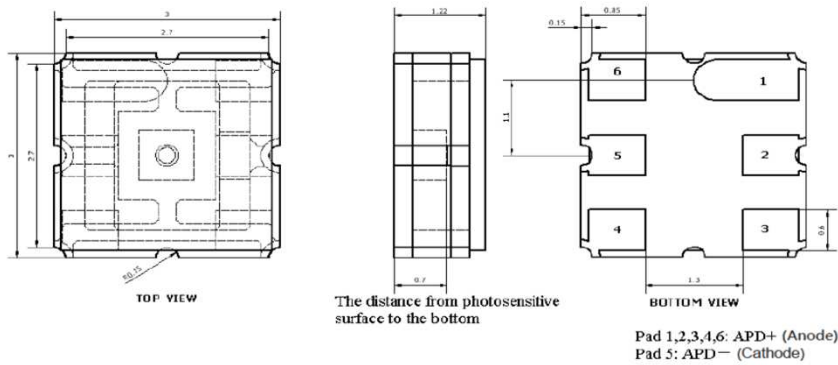
Parameters	Symbol	Min	Typ	Max	Unit	Test conditions
Sensitivity range	$\lambda$	400		1100	nm	
Active area	$I_{\text{PH}}$		$\varnothing 500$		$\mu\text{m}$	
Responsivity	$S_{\lambda}$	35	50		A/W	$\Phi_e = 1 \mu\text{W}$ , M=100, $\lambda = 800 \text{ nm}$
Rise time	$t_{\text{R}}$		0.3		ns	f=1 MHz, $R_{\text{L}} = 50 \Omega$ , $\lambda = 800 \text{ nm}$
Dark current	$I_{\text{D}}$	0.05	0.1	0.5	nA	M=100
Capacitance	$C_{\text{j}}$		3		pF	M=100, 1 MHz
Optimal gain	M		100			
Breakdown voltage	$V_{\text{BR}}$	120		160	V	$I_{\text{R}} = 2 \mu\text{A}$
Temperature coefficient	TKV		0.9		V/K	$T = -40 \dots +85$

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

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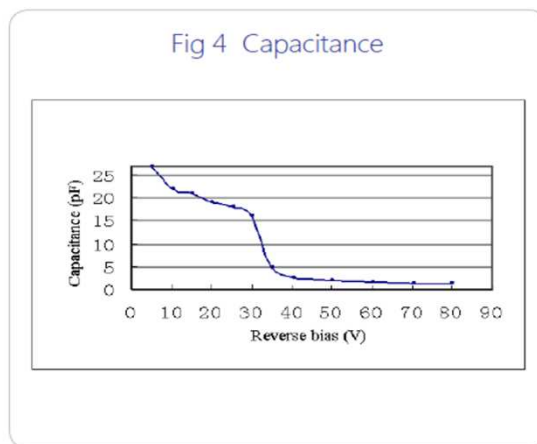
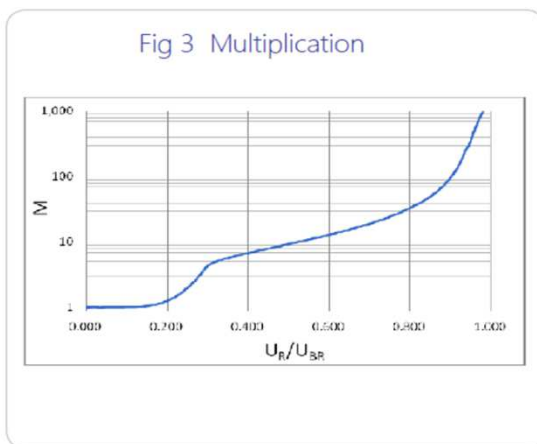
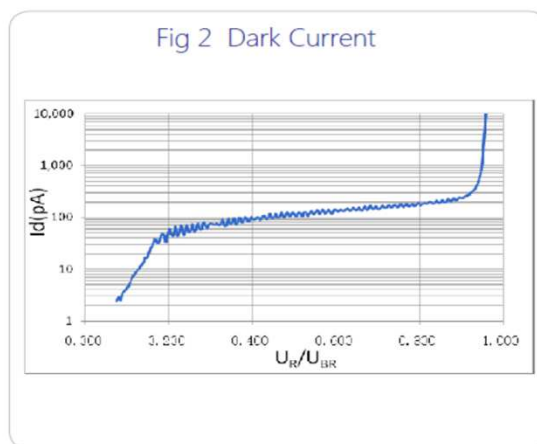
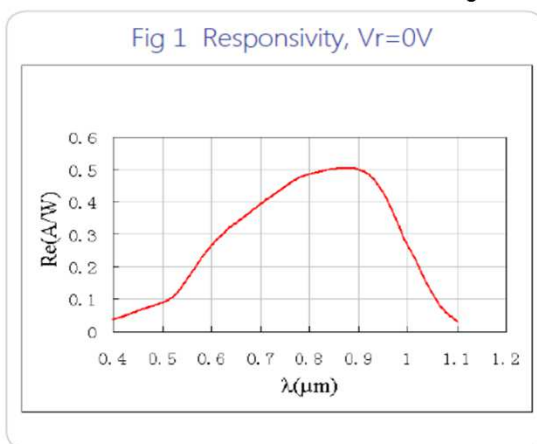
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**EOAPD-800-1-07**



Unit: mm, Tolerance: ±0.2

Package dimensions in mm

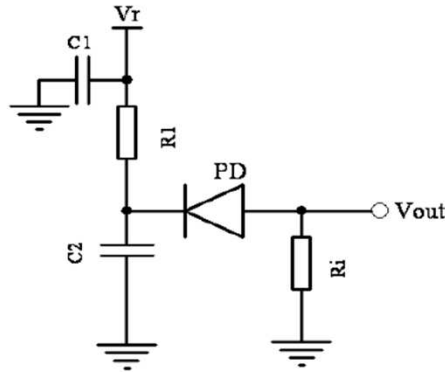


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**EOAPD-800-1-07**

Applications Diagram



Notes: C1 - Filter capacitor, filter noise from  $V_r$ .

C2 - bypass capacitor, the loop to ground for AC signal.

R1 - current-limiting resistor, protect APD from higher voltage.

$R_i$  - sampling resistor, convert the current signal into a voltage signal.